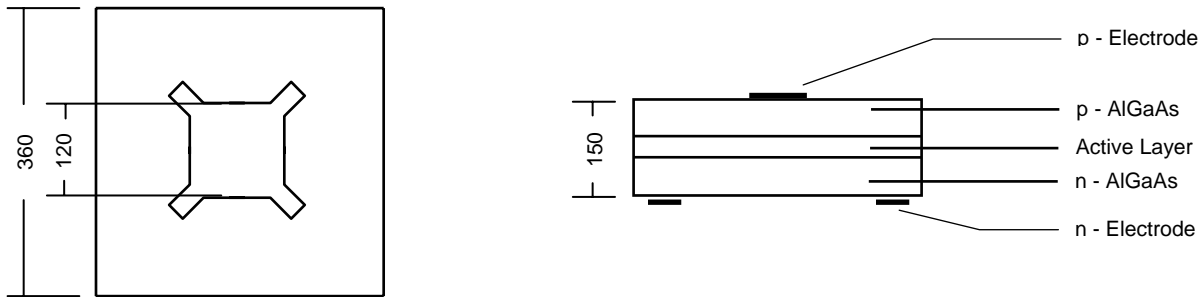


TCS810P



- ❖ Features:
AlGaAs (DHS) / AlGaAs - substrate removed

- ❖ Outline Dimensions:



- ❖ Physical Structure:

Chip dimensions		Chip size	14 mil x 14 mil	360 μm x 360 μm
		Thickness	5.9 mil	150 μm
		Bonding Pad	4.7 mil	120 μm
Electrode	Top	P (anode)	Gold alloy	
	Backside	N (cathode)	Gold alloy	

- ❖ Electro-Optical Characteristics:

Parameter	Symb ol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	1.50	2.00	V
Reverse Voltage	V_R	$I_R = 10\text{mA}$	5	-	-	V
Peak Wavelength	λ_p	$I_F = 20\text{mA}$	-	810	-	nm
Output power	P_O	$I_F = 20\text{mA}$	2.5	3.2	-	mW